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Docket No. 0819-0425

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Haruko INOUE et al.)

Serial No. 09/666,156)

Filed: September 19, 2000)

For: HIGH-VOLTAGE MOS)

TRANSISTOR AND METHOD)

FOR FABRICATING THE SAME)

) Group Art Unit: 2811

) Examiner: S. Loke

CERTIFICATE OF MAILING

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VLS

RESPONSE TO ELECTION REQUIREMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the election requirement in the Office Action of February 20, 2002,
Applicants hereby elect without traverse the Group I claims - that is, claims 1-7, drawn to a
semiconductor device.

Examination on the merits is requested.

Respectfully submitted,

[Signature]

Eric J. Robinson
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